

2N3903, 2N3904

2N3903 is a Preferred Device

General Purpose Transistors

NPN Silicon



ON Semiconductor™

<http://onsemi.com>

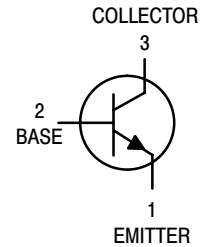
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

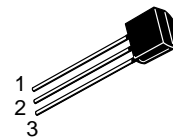
THERMAL CHARACTERISTICS (Note 1.)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

1. Indicates Data in addition to JEDEC Requirements.

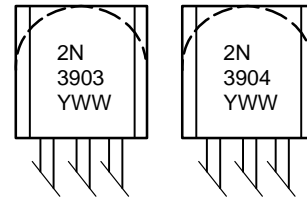


STYLE 1



TO-92
CASE 29
STYLE 1

MARKING DIAGRAMS



Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
2N3903	TO-92	5000 Units/Box
2N3903RLRM	TO-92	2000/Ammo Pack
2N3904	TO-92	5000 Units/Box
2N3904RLRA	TO-92	2000/Tape & Reel
2N3904RLRE	TO-92	2000/Tape & Reel
2N3904RLRM	TO-92	2000/Ammo Pack
2N3904RLRP	TO-92	2000/Ammo Pack
2N3904RL1	TO-92	2000/Tape & Reel
2N3904ZL1	TO-92	2000/Ammo Pack

Preferred devices are recommended choices for future use and best overall value.

2N3903, 2N3904

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 2.) (I _C = 1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	40	–	V _{dc}
Collector–Base Breakdown Voltage (I _C = 10 μA _{dc} , I _E = 0)	V _{(BR)CBO}	60	–	V _{dc}
Emitter–Base Breakdown Voltage (I _E = 10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	6.0	–	V _{dc}
Base Cutoff Current (V _{CE} = 30 V _{dc} , V _{EB} = 3.0 V _{dc})	I _{BL}	–	50	nA _{dc}
Collector Cutoff Current (V _{CE} = 30 V _{dc} , V _{EB} = 3.0 V _{dc})	I _{CEX}	–	50	nA _{dc}

ON CHARACTERISTICS

DC Current Gain (Note 2.) (I _C = 0.1 mA _{dc} , V _{CE} = 1.0 V _{dc})	2N3903	h _{FE}	20	–	–
	2N3904		40	–	–
(I _C = 1.0 mA _{dc} , V _{CE} = 1.0 V _{dc})	2N3903	35	–	–	–
	2N3904	70	–	–	–
(I _C = 10 mA _{dc} , V _{CE} = 1.0 V _{dc})	2N3903	50	150	–	–
	2N3904	100	300	–	–
(I _C = 50 mA _{dc} , V _{CE} = 1.0 V _{dc})	2N3903	30	–	–	–
	2N3904	60	–	–	–
(I _C = 100 mA _{dc} , V _{CE} = 1.0 V _{dc})	2N3903	15	–	–	–
	2N3904	30	–	–	–
Collector–Emitter Saturation Voltage (Note 2.) (I _C = 10 mA _{dc} , I _B = 1.0 mA _{dc}) (I _C = 50 mA _{dc} , I _B = 5.0 mA _{dc})		V _{CE(sat)}	–	0.2	V _{dc}
			–	0.3	
Base–Emitter Saturation Voltage (Note 2.) (I _C = 10 mA _{dc} , I _B = 1.0 mA _{dc}) (I _C = 50 mA _{dc} , I _B = 5.0 mA _{dc})		V _{BE(sat)}	0.65	0.85	V _{dc}
			–	0.95	

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I _C = 10 mA _{dc} , V _{CE} = 20 V _{dc} , f = 100 MHz)	2N3903	f _T	250	–	MHz
	2N3904		300	–	
Output Capacitance (V _{CB} = 5.0 V _{dc} , I _E = 0, f = 1.0 MHz)		C _{obo}	–	4.0	pF
Input Capacitance (V _{EB} = 0.5 V _{dc} , I _C = 0, f = 1.0 MHz)		C _{ibo}	–	8.0	pF
Input Impedance (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	2N3903	h _{ie}	1.0	8.0	k Ω
	2N3904		1.0	10	
Voltage Feedback Ratio (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	2N3903	h _{re}	0.1	5.0	X 10 ^{–4}
	2N3904		0.5	8.0	
Small–Signal Current Gain (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	2N3903	h _{fe}	50	200	–
	2N3904		100	400	
Output Admittance (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)		h _{oe}	1.0	40	μmhos
Noise Figure (I _C = 100 μA _{dc} , V _{CE} = 5.0 V _{dc} , R _S = 1.0 k Ω, f = 1.0 kHz)	2N3903	NF	–	6.0	dB
	2N3904		–	5.0	

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 3.0 V _{dc} , V _{BE} = 0.5 V _{dc} , I _C = 10 mA _{dc} , I _{B1} = 1.0 mA _{dc})	2N3903 2N3904	t _d	–	35	ns
Rise Time			t _r	–	35	ns
Storage Time	(V _{CC} = 3.0 V _{dc} , I _C = 10 mA _{dc} , I _{B1} = I _{B2} = 1.0 mA _{dc})	2N3903 2N3904	t _s	–	175	ns
Fall Time			t _f	–	50	ns

2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

2N3903, 2N3904

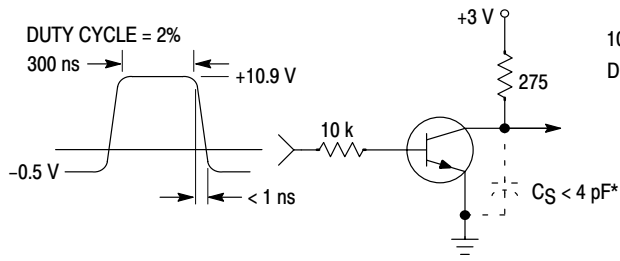


Figure 1. Delay and Rise Time Equivalent Test Circuit

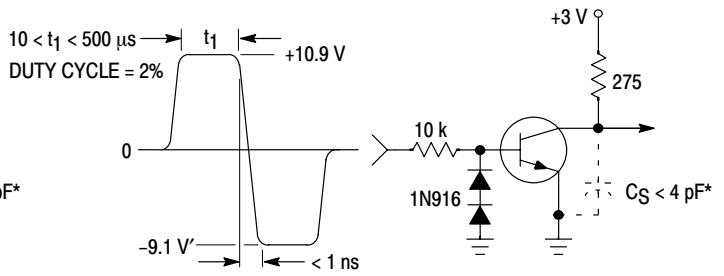


Figure 2. Storage and Fall Time Equivalent Test Circuit

* Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

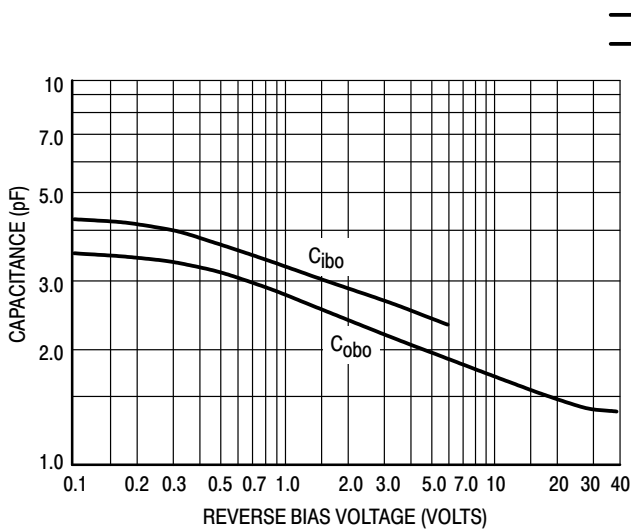


Figure 3. Capacitance

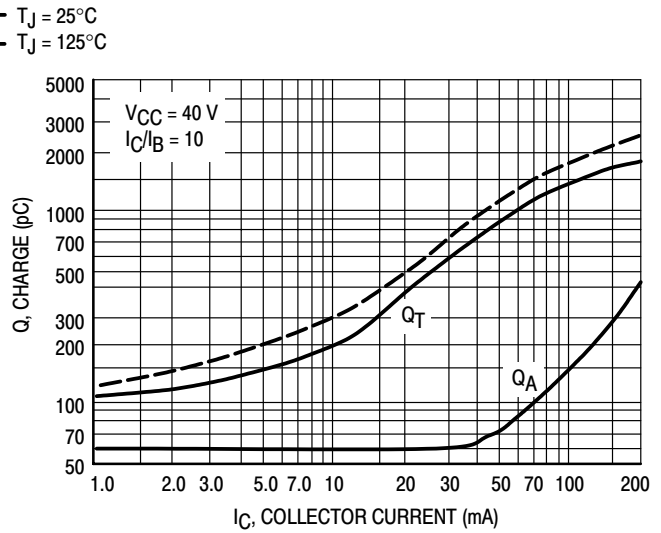


Figure 4. Charge Data

2N3903, 2N3904

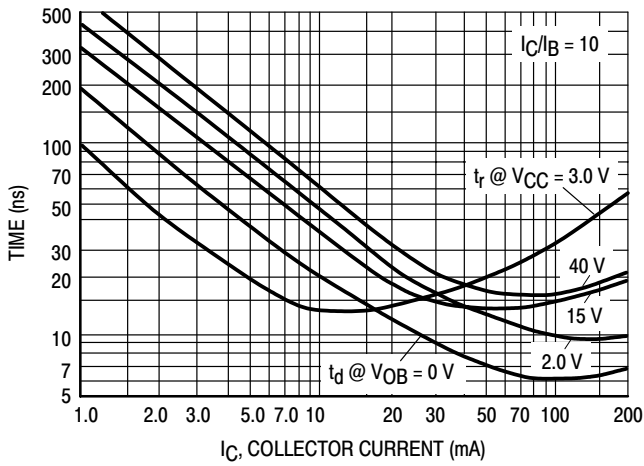


Figure 5. Turn-On Time

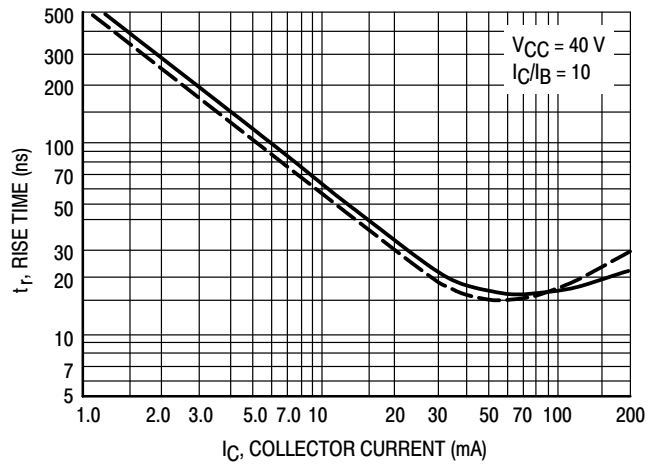


Figure 6. Rise Time

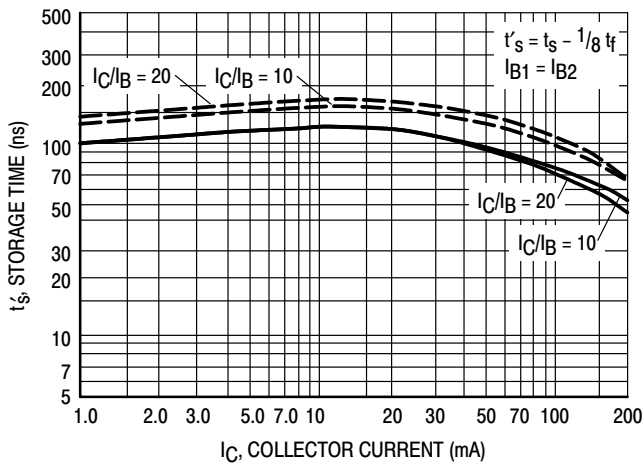


Figure 7. Storage Time

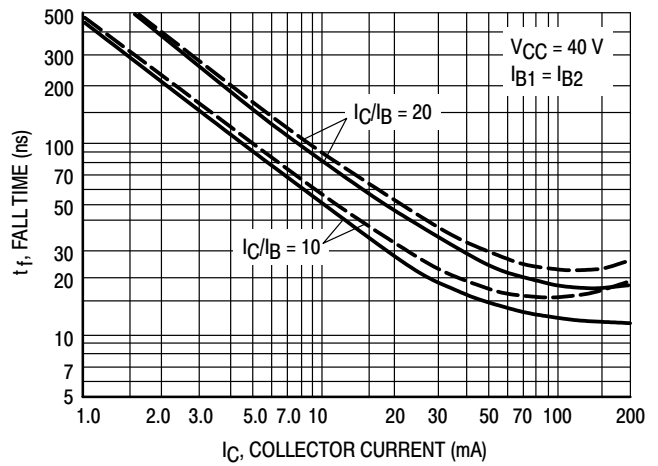


Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

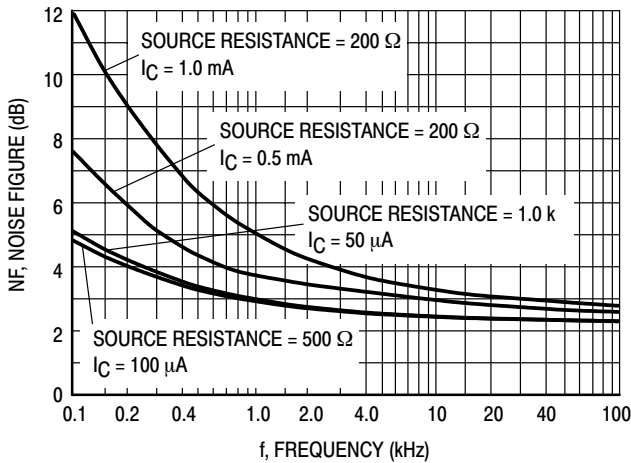


Figure 9.

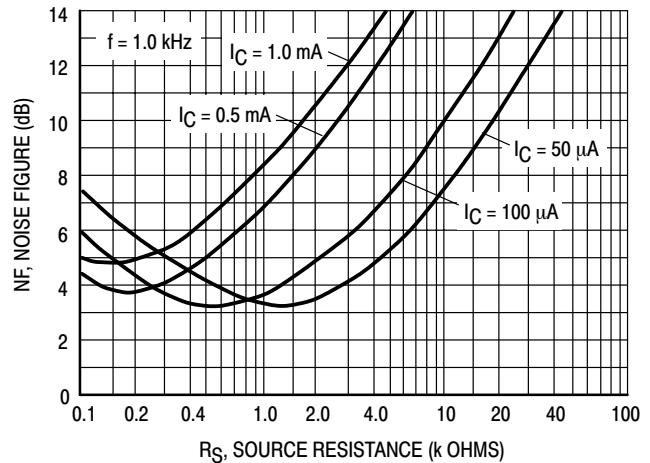


Figure 10.

2N3903, 2N3904

h PARAMETERS

($V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$)

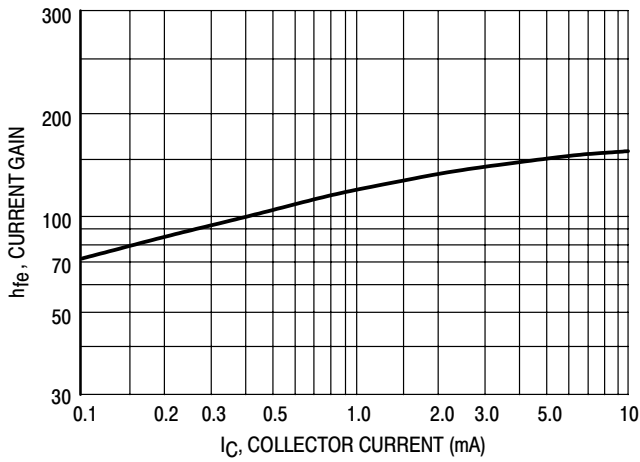


Figure 11. Current Gain

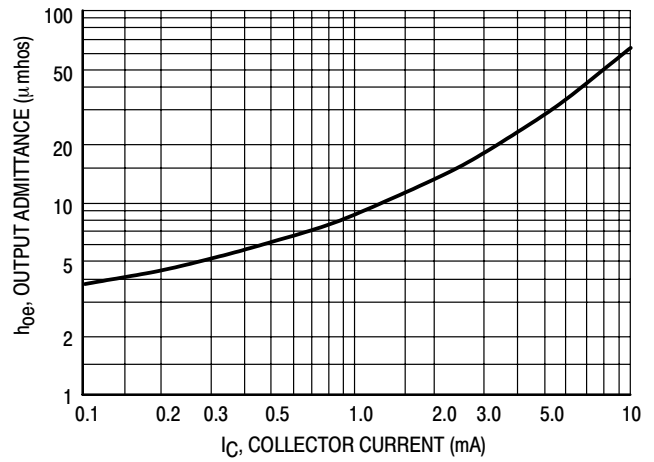


Figure 12. Output Admittance

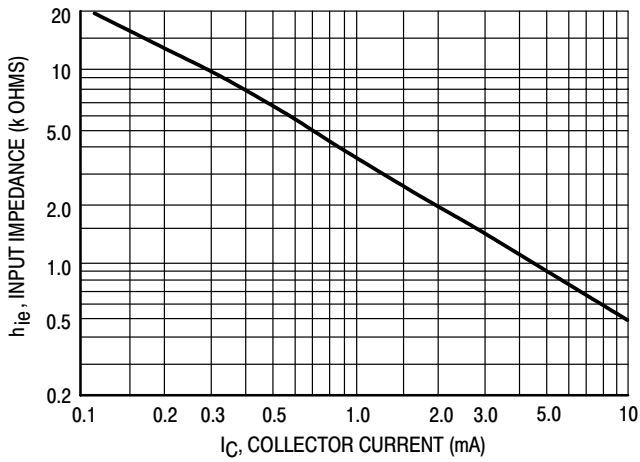


Figure 13. Input Impedance

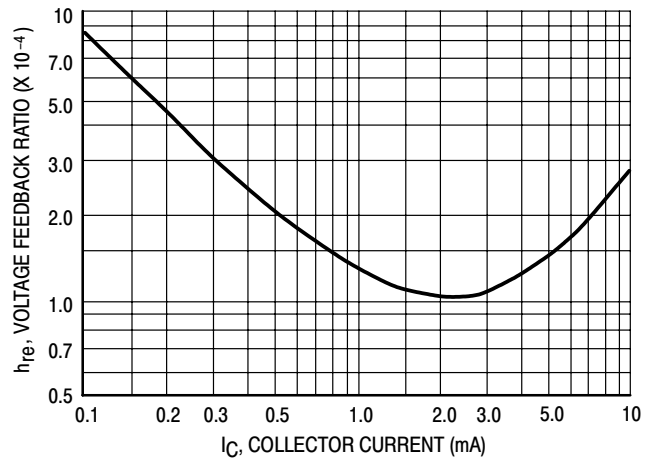


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

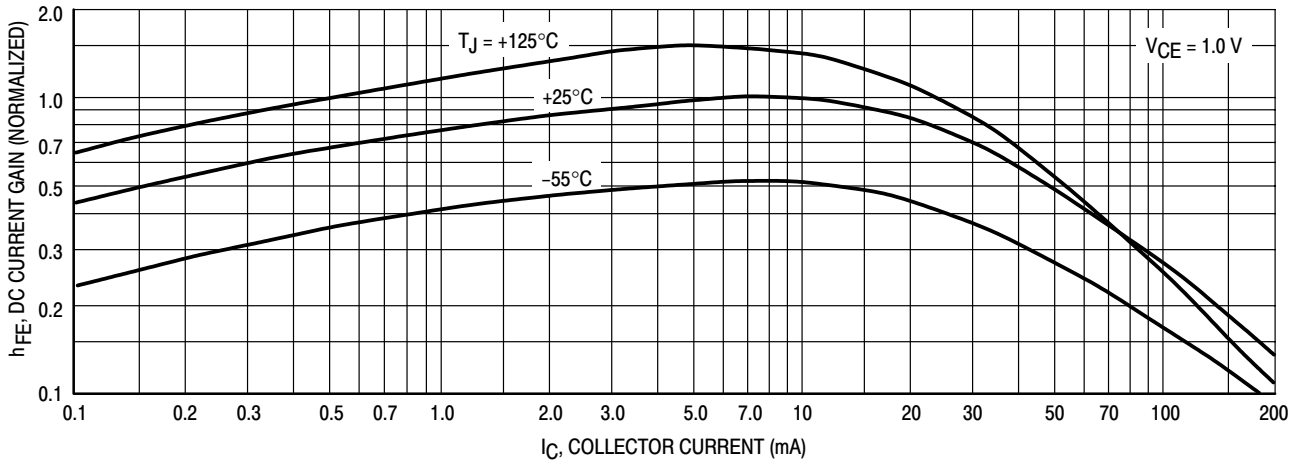


Figure 15. DC Current Gain

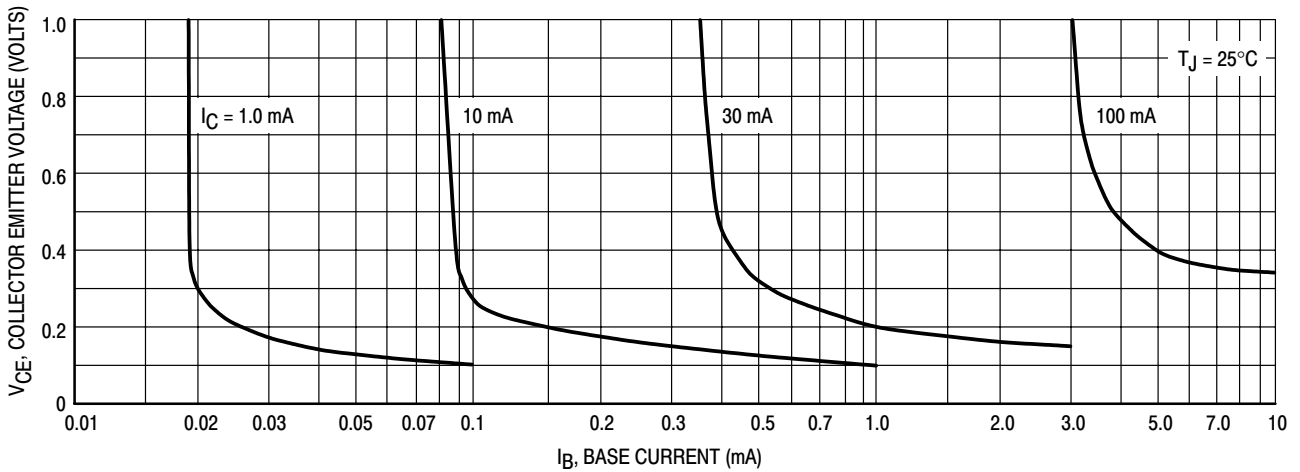


Figure 16. Collector Saturation Region

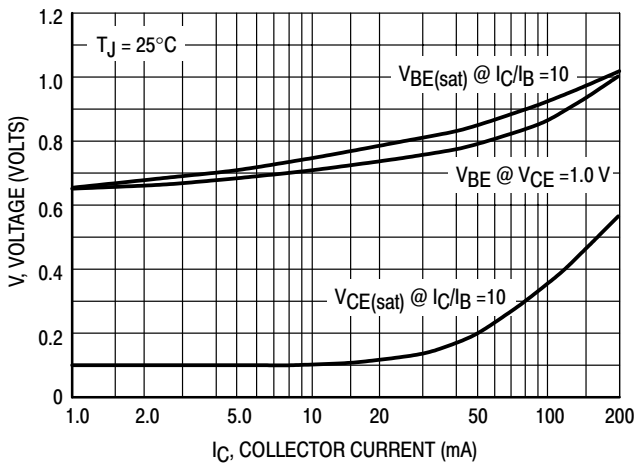


Figure 17. "ON" Voltages

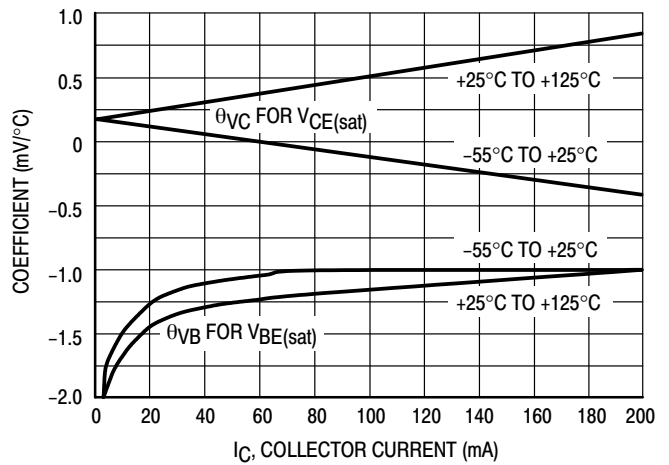
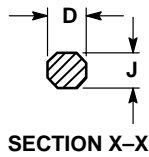
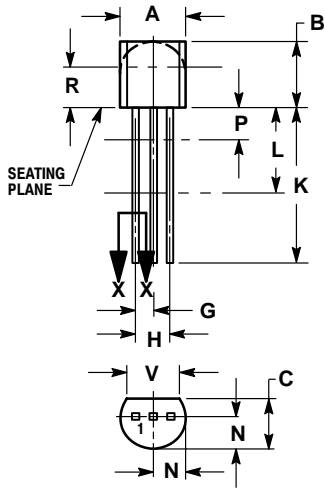


Figure 18. Temperature Coefficients

2N3903, 2N3904

PACKAGE DIMENSIONS

TO-92
TO-226AA
CASE 29-11
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

- PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 14:

- PIN 1. EMITTER
2. COLLECTOR
3. BASE

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center
4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.